



# BSS84

### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(on)</sub> max     | <b>Ι</b> <sub>D</sub><br>Τ <sub>A</sub> = +25°C |
|-------------------|-----------------------------|---|
| -50V              | 10Ω @ V <sub>GS</sub> = -5V | -130mA  |

## **Description and Applications**

This MOSFET has been designed to minimize on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

### P-CHANNEL ENHANCEMENT MODE MOSFET

#### Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/guality/product-definitions/

 An Automotive-Compliant Part is Available Under Separate Datasheet (<u>BSS84Q</u>)

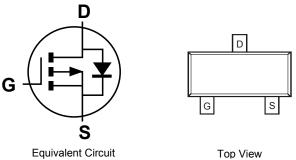
#### **Mechanical Data**

- Case: SOT23 (Standard)
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



SOT23

Top View



### Ordering Information (Note 4)

| Part Number | Case             | Packaging         |
|-------------|------------------|-------------------|
| BSS84-7-F   | SOT23 (Standard) | 3000/Tape & Reel  |
| BSS84-13-F  | SOT23 (Standard) | 10000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



### **Marking Information**



K84 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$  = Month (ex: 9 = September)

| Date Code Key |      |     |      |          |          |          |          |      |      |      |      |          |
|---------------|------|-----|------|----------|----------|----------|----------|------|------|------|------|----------|
| Year          | 1998 |     | 2021 | 2022     | 2023     | 2024     | 2025     | 2026 | 2027 | 2028 | 2029 | 2030     |
| Code          | J    |     |      | J        | К        | L        | М        | Ν    | 0    | Р    | R    | S        |
|               |      |     |      |          |          |          |          |      |      | -    |      |          |
| Month         | Jan  | Feb | Mar  | Apr      | Mav      | Jun      | Jul      | Aug  | Sep  | Oct  | Nov  | Dec      |
| Month<br>Code | Jan  | Feb | Mar  | Apr<br>4 | May<br>5 | Jun<br>6 | Jul<br>7 | Aug  | Sep  | Oct  | Nov  | Dec<br>D |

### Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol     | Value            | Unit |    |
|--|------------|------------------|------|----|
| Drain-Source Voltage                       |            | V <sub>DSS</sub> | -50  | V  |
| Drain-Gate Voltage $R_{GS} \le 20 k\Omega$ |            | V <sub>DGR</sub> | -50  | V  |
| Gate-Source Voltage                        | Continuous | V <sub>GSS</sub> | ±20  | V  |
| Drain Current (Note 5)                     | Continuous | ID               | -130 | mA |
| Pulsed Drain Current                       |            | I <sub>DM</sub>  | -1.2 | A  |

### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)        | PD                                | 300         | mW   |
| Thermal Resistance, Junction to Ambient | R <sub>0JA</sub>                  | 417         | °C/W |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

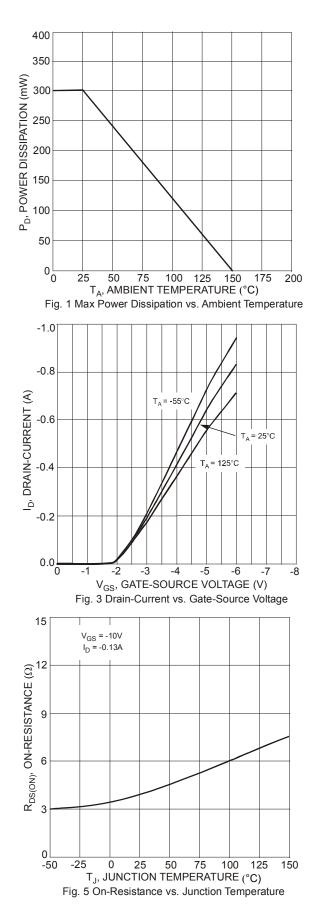
### Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                              | Symbol              | Min  | Тур  | Max  | Unit | Test Condition  |  |
|---|---------------------|------|------|------|------|---|--|
| OFF CHARACTERISTICS (Note 6)                |                     |      |      |      |      | ·   |  |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>   | -50  |      | _    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA                         |  |
|   |                     | _    |      | -1   | μA   | V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C  |  |
| Zero Gate Voltage Drain Current             | IDSS                |      | —    | -2   | μA   | V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C |  |
|   |                     |      |      | -100 | nA   | $V_{DS}$ = -25V, $V_{GS}$ = 0V, $T_{J}$ = +25°C                       |  |
| Gate-Body Leakage                           | IGSS                |      | —    | ±10  | nA   | $V_{GS} = \pm 20V, V_{DS} = 0V$                                       |  |
| ON CHARACTERISTICS (Note 6)                 |                     |      |      |      |      |   |  |
| Gate Threshold Voltage                      | V <sub>GS(th)</sub> | -0.8 | —    | -2.0 | V    | $V_{DS} = V_{GS}$ , $I_D = -1mA$                                      |  |
| Static Drain-Source On-Resistance           | R <sub>DS(on)</sub> | —    | 3.2  | 10   | Ω    | V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.100A                       |  |
| Forward Transconductance                    | <b>g</b> fs         | 0.05 | _    | _    | S    | V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A                        |  |
| DYNAMIC CHARACTERISTICS (Note 7)            |                     |      |      |      |      |   |  |
| Input Capacitance                           | C <sub>iss</sub>    | _    | 24.6 | 45   | pF   |   |  |
| Output Capacitance                          | Coss                | _    | 4.7  | 25   | pF   | V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz              |  |
| Reverse Transfer Capacitance                | C <sub>rss</sub>    | _    | 2.8  | 12   | pF   | 1   |  |
| Gate Resistance                             | Rq                  | _    | 916  |      | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                  |  |
| Total Gate Charge (V <sub>GS</sub> = -4.5V) | Qg                  | _    | 0.28 | _    | nC   |   |  |
| Total Gate Charge (V <sub>GS</sub> = -10V)  | Qq                  |      | 0.59 |      | nC   |   |  |
| Gate-Source Charge                          | Qqs                 |      | 0.09 |      | nC   | $V_{DS} = -10V, I_D = -0.1A$  |  |
| Gate-Drain Charge                           | Q <sub>gd</sub>     |      | 0.08 |      | nC   |   |  |
| Turn-On Delay Time                          | t <sub>D(on)</sub>  |      | 10   |      | ns   | V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A,                      |  |
| Turn-Off Delay Time                         | t <sub>D(off)</sub> | _    | 18   | —    | ns   | $R_{GEN} = 50\Omega, V_{GS} = -10V$                                   |  |

5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found Notes: on our website at http://www.diodes.com/package-outlines.html.

6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.





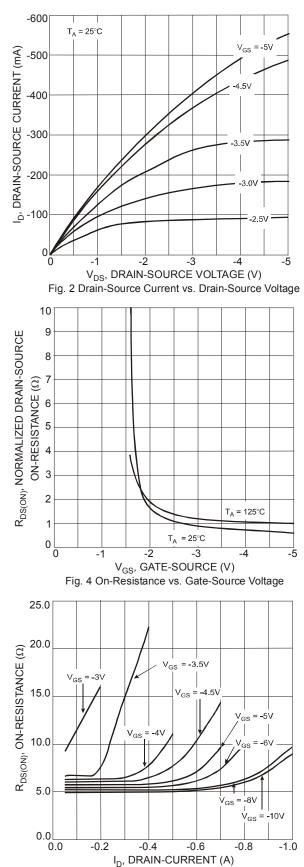
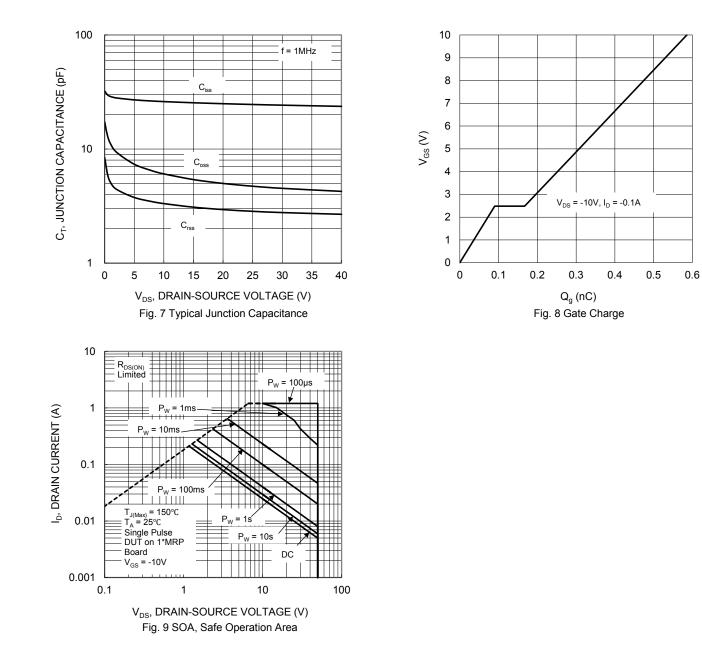


Fig. 6 On-Resistance vs. Drain-Current

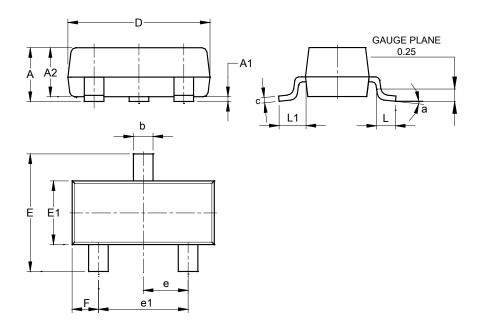






### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

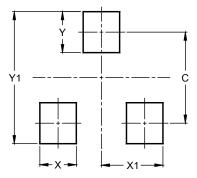


| S   | SOT23 (Standard)     |       |       |  |  |  |  |
|-----|----------------------|-------|-------|--|--|--|--|
| Dim | Min                  | Max   | Тур   |  |  |  |  |
| Α   | 0.90                 | 1.15  | 1.025 |  |  |  |  |
| A1  | 0.00                 | 0.10  | 0.05  |  |  |  |  |
| A2  | 0.85                 | 1.10  | 0.975 |  |  |  |  |
| b   | 0.30                 | 0.51  | 0.40  |  |  |  |  |
| С   | 0.080                | 0.202 | 0.11  |  |  |  |  |
| D   | 2.80                 | 3.00  | 2.90  |  |  |  |  |
| Е   | 2.25                 | 2.55  | 2.40  |  |  |  |  |
| E1  | 1.20                 | 1.40  | 1.30  |  |  |  |  |
| е   | 0.89                 | 1.03  | 0.915 |  |  |  |  |
| e1  | 1.78                 | 2.05  | 1.83  |  |  |  |  |
| F   | 0.40                 | 0.60  | 0.535 |  |  |  |  |
| L1  | 0.45                 | 0.61  | 0.55  |  |  |  |  |
| L   | 0.25                 | 0.55  | 0.40  |  |  |  |  |
| а   | 0°                   | 8°    |       |  |  |  |  |
| All | All Dimensions in mm |       |       |  |  |  |  |

### Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23 (Standard)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Y          | 0.9           |
| Y1         | 2.9           |

# SOT23 (Standard)



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